

DESCRIPTION

Title of Invention:

ADHESIVE SHEET FOR BACKGRINDING, SEMICONDUCTOR WAFER
MANUFACTURING METHOD, AND SUBSTRATE SHEET

Technical Field

[0001]

The present invention relates to an adhesive sheet for back grinding, a method for manufacturing a semiconductor wafer using the same, and a base material sheet.

Background Art

[0002]

When a semiconductor wafer is processed, an adhesive sheet is adhered to the wafer to protect it from damage. For example, in the back grinding step for the semiconductor wafer, the adhesive sheet is adhered to the semiconductor wafer to protect the pattern surface thereof. The adhesive sheet is required to have followability to follow unevenness of the pattern surface (bump followability) in terms of adhesiveness to the uneven pattern surface such as a protruding electrode (bump) and reliability of pattern surface protection.

[0003]

As an adhesive sheet having the followability, adhesive sheets with a thicker adhesive or a flexible resin layer with cushioning properties between a base material film and an adhesive are common in the market. However, when the unevenness of the pattern surface is significant, risks of insufficient followability and adhesive residue increase.

[0004]

In Patent Literature 1, an adhesive sheet is configured to have an adhesive layer with an opening part having a diameter smaller than an outer diameter of a semiconductor wafer on one side of a base material layer, the adhesive layer is adhered to the outer peripheral part of the semiconductor wafer so that the convex part of the semiconductor wafer is placed in the opening part of the adhesive layer by vacuum mounting, and the convex part is embedded in the base material layer, which prevents adhesive residue and deterioration of the protective function.

Citation List

Patent Literature

[0005]

[Patent Literature 1] JP-A-2019-140387

Summary of Invention

Technical Problem

[0006]

The inventors of the present invention conducted an intensive study on the adhesive layer disclosed in Patent Literature 1 and

found that the base material layer may not sufficiently follow the convex part.
[0007]

The present invention was made in consideration of these circumstances, and aims to provide an adhesive sheet for back grinding capable of enhance followability of a base material layer to a convex part of a semiconductor wafer.

Solution to Problem

[0008]

According to the present invention, provided are:

- (1) an adhesive sheet for back grinding of a semiconductor wafer having a convex part, comprising: a base material layer; and an adhesive layer provided on the base material layer, wherein: the adhesive layer comprises an opening part having a diameter smaller than a diameter of the semiconductor wafer; the adhesive layer is adhered to an outer peripheral part of the semiconductor wafer such that the convex part of the semiconductor wafer is placed in the opening part; the adhesive layer is configured so that the convex part is protected by the base material layer with the semiconductor wafer adhered to the adhesive layer; the base material layer comprises a cushion layer and a barrier layer; and an oxygen permeability of the base material layer at 25°C and at RH0% measured base on JIS K 7126-2 (isobaric method) is 1000 ml/(m²·24h·atm) or lower,
- (2) the adhesive sheet of (1), wherein the barrier layer is provided on an opposite side of the adhesive layer as viewed from the cushion layer,
- (3) the adhesive sheet of (1) or (2), wherein the convex part is protected by being embedded in the base material layer,
- (4) the adhesive sheet of any one of (1) to (3), wherein the semiconductor wafer is adhered to the adhesive layer under reduced pressure,
- (5) a method for manufacturing a semiconductor wafer using the adhesive sheet of any one of (1) to (4), comprising: a frame adhering step; a wafer adhering step; a heating step; a cutting step; a resin curing step; and a grinding step, wherein: in the frame adhering step, the adhesive sheet is adhered to a ring frame; in the wafer adhering step, the adhesive sheet is adhered to the outer peripheral part of the semiconductor wafer under reduced pressure, the outer peripheral part on a surface of the semiconductor wafer where the convex part is provided; in the heating step, the base material layer is heated; in the cutting step, the adhesive sheet is cut along an outer periphery of the semiconductor wafer; in the resin curing step, the base material layer is brought in contact with a curable resin after the wafer adhering step, and the curable resin is cured in that state; and in the grinding step, a backside of the semiconductor wafer is ground, and
- (6) a base material sheet, comprising: a cushion layer; and a barrier layer, wherein an oxygen permeability of the base material

layer at 25°C and at RH0% measured base on JIS K 7126-2 (isobaric method) is 1000 ml/(m²·24h·atm) or lower.

[0009]

The inventors of the present invention conducted an intensive study and found that the oxygen permeability of the base material layer is reduced by providing the barrier layer, which solve the above-described problems, leading to the completion of the present invention.

Brief Description of Drawings

[0010]

Fig. 1 is a cross-sectional view showing a state before adhering a ring frame 3 to an adhesive sheet 10 of one embodiment of the present invention.

Fig. 2 is a cross-sectional view showing a state after adhering the ring frame 3 to the adhesive sheet 10 from the state in Fig. 1.

Fig. 3 is a cross-sectional view showing a state after adhering a semiconductor wafer 4 to the adhesive sheet 10 and placing it inside a decompression chamber 16 from the state in Fig. 2.

Fig. 4 is a cross-sectional view showing a state after removing the semiconductor wafer 4 to which the adhesive sheet 10 is adhered from the decompression chamber 16 from the state in Fig. 3.

Fig. 5 is a cross-sectional view showing a state after removing the ring frame 3 and sucking the semiconductor wafer 4 by a decompression unit 6 from the state in Fig. 4.

Fig. 6 is a cross-sectional view showing a state in which the adhesive sheet 10 is pressed against a curable resin 8 and the curable resin 8 is being cured from the state in Fig. 5.

Fig. 7 is a cross-sectional view showing a state after completion of curing the curable resin 8 from the state in Fig. 6.

Fig. 8 is a cross-sectional view showing a state after grinding a backside 4b of the semiconductor wafer 4 from the state in Fig. 7.

Fig. 9 is a cross-sectional view showing a state after peeling the semiconductor wafer 4 from the adhesive sheet 10 from the state in Fig. 8.

Fig. 10 is a cross-sectional view showing a base material sheet 11 of one embodiment of the present invention.

Description of Embodiments

[0011]

Hereinafter, embodiments of the present invention will be described. Various features shown in the following embodiments can be combined with each other. In addition, the invention can be made independently for each feature.

[0012]

1. Adhesive Sheet

An adhesive sheet 10 of one embodiment of the present invention will be described using Figs. 1 to 9. The adhesive sheet

10 of the present embodiment has a base material layer 1 and an adhesive layer 2 provided on the base material layer 1. The adhesive sheet 10 is used to grind a backside 4b of a semiconductor wafer 4 having a convex part 5. Hereinafter, each configuration will be described.

[0013]

1-1. Base Material Layer 1

As shown in Fig. 1, the base material layer 1 has a cushion layer 1a, a surface treatment layer 1b, and a barrier layer 1c. The surface treatment layer 1b is provided on the cushion layer 1a. The barrier layer 1c is preferably provided on the opposite side of the surface treatment layer 1b (or the adhesive layer 2) as viewed from the cushion layer 1a. The barrier layer 1c is preferably adhered to the cushion layer 1a via an unshown adhesive layer. The surface treatment layer 1b can be omitted.

[0014]

The entire thickness of the base material layer 1 is preferably 50 to 400 μm , more preferably 100 to 350 μm , and even more preferably 200 to 300 μm . The thickness is, specifically for example, 50, 100, 150, 200, 250, 300, 350, or 400 μm , and may be in the range between the two values exemplified herein.

[0015]

<Cushion Layer 1a>

The cushion layer 1a is a layer for protecting the convex part 5 of the semiconductor wafer 4 shown in Fig. 2. The cushion layer 1a is preferably configured of a thermoplastic resin. The composition of the thermoplastic resin is not particularly limited. Examples of the thermoplastic resin that can be used include ionomer resins in which the carboxyl groups of a simple substance and/or composite such as ethylene-methacrylic acid-acrylic ester ternary copolymers, ethylene-methacrylic acid copolymers, and ethylene-acrylic acid copolymers are cross-linked by metal ions such as sodium ions, lithium ions, and magnesium ions; soft polypropylene resins blended with styrene-butadiene copolymer rubber, styrene-butadiene-styrene block copolymer rubber, styrene-isoprene-styrene block copolymer rubber, ethylene-propylene rubber, or the like; low density polyethylene; ethylene-propylene block copolymer; ethylene-propylene random copolymer; ethylene-vinyl acetate copolymer; ethylene-methacrylic acid copolymer; ethylene-1 octene copolymer; and polybutene. Among these, ionomer resins are preferred.

[0016]

The ratio R_a (mass %) of the (meth)acrylic monomer unit in the resin configuring the cushion layer 1a is preferably lower than the ratio R_b (mass %) of the (meth)acrylic monomer unit in the acrylic resin configuring the surface treatment layer 1b. In this case, the technical significance of providing the surface treatment layer 1b is prominent because the adhesion between the adhesive layer 2 and the surface treatment layer 1b that are configured with the acrylic resin compositions is higher than that between the adhesive layer 2 and the cushion layer 1a. The value of $(R_b - R_a)$ is, for example, 10 to 100 mass%, and preferably 30

to 100 mass%. This value is, specifically for example, 10, 20, 30, 40, 50, 60, 70, 80, 90, or 100 mass%, and may be in the range between the two values exemplified herein.

[0017]

The storage modulus E'a of the cushion layer 1a at 180°C is preferably lower than the storage modulus E'b of the surface treatment layer 1b at 180°C. When the storage modulus E'a of the cushion layer 1a is low under a high temperature condition, the cushion layer 1a is likely to be excessively softened during heating and strongly adhered to the wafer, resulting in difficulty in peeling. Occurrence of such a problem is suppressed by providing the surface treatment layer 1b. Therefore, the technical significance of providing the surface treatment layer 1b is prominent when the storage modulus E'a is lower than the storage modulus E'b. When the storage modulus E'a cannot be measured due to melting of the cushion layer 1a, the storage modulus E'a is taken as 0 for convenience.

[0018]

The weight average molecular weight (Mw) of the above-described thermoplastic resin is preferably 10000 to 1000000, and more preferably 50000 to 500000. The weight average molecular weight (Mw) is a value in terms of polystyrene measured by gel permeation chromatography (GPC).

[0019]

The softening temperature (JIS K7206) of the above-described thermoplastic resin is preferably 45 to 200°C, and more preferably 55 to 150°C. The softening temperature is, specifically for example, 45, 50, 55, 60, 65, 70, 75, 80, 90, 100, 110, 120, 130, 140, 150, 160, 170, 180, 190, or 200°C, and may be in the range between the two values exemplified herein.

[0020]

The melting point (JIS K7121) of the above-described thermoplastic resin is preferably 60 to 200°C, and more preferably 80 to 150°C. The melting point is, specifically for example, 60, 70, 80, 90, 100, 110, 120, 130, 140, 150, 160, 170, 180, 190, or 200°C, and may be in the range between the two values exemplified herein.

[0021]

The melt flow rate (MFR) (JIS K7210, 125°C/10.0 kg load) of the above-described thermoplastic resin is 0.2 to 30 g/10 min, and more preferably 0.3 to 20 g/10 min.

[0022]

When the thermoplastic resin has the properties as described above, the cushion layer 1a is moderately softened as the base material layer 1 is heated, making it easy to embed the convex part 5 in the base material layer 1.

[0023]

The thickness of the cushion layer 1a is preferably 50 to 400 μm , more preferably 100 to 350 μm , and even more preferably 200 to 300 μm . The thickness is, specifically for example, 50, 100, 150, 200, 250, 300, 350, or 400 μm , and may be in the range between the two values exemplified herein.

[0024]

<Surface Treatment Layer 1b>

The surface treatment layer 1b is formed of an acrylic resin composition containing an acrylic resin, and cross-linked by light irradiation or heating. When the adhesive layer 2 is formed directly on the cushion layer 1a, peeling of the adhesive layer 2 may occur if the adhesion between the cushion layer 1a and the adhesive layer 2 is not good. However, the peeling of the adhesive layer 2 can be suppressed by forming the surface treatment layer 1b on the cushion layer 1a and by forming the adhesive layer 2 with an acrylic resin composition.

[0025]

When corona discharge treatment is applied to the cushion layer 1a to improve the adhesion between the cushion layer 1a and the adhesive layer 2, and this cushion layer 1a is adhered to a semiconductor wafer, the adhesive force between the cushion layer 1a and the semiconductor wafer may become too high, making it difficult to peel the semiconductor wafer from the cushion layer 1a. In the present embodiment, the surface treatment layer 1b is formed on the cushion layer 1a, and the surface treatment layer 1b is adhered to a semiconductor wafer. As described above, since the surface treatment layer 1b has excellent adhesion to the adhesive layer 2 without corona discharge treatment, corona discharge treatment is not required for the surface treatment layer 1b. For this reason, the adhesive force between the base material layer 1 and the semiconductor wafer can be reduced by providing the surface treatment layer 1b.

[0026]

Specifically, the adhesive force measured in accordance with JIS Z0237 at 23°C between the base material layer 1 and the semiconductor wafer after heating the semiconductor wafer to which the base material layer 1 of the test piece cut from the adhesive sheet 10 is adhered for 1 minute at 100°C and cooling to room temperature can be lower than 6 N/200 mm by providing the surface treatment layer 1b. In this case, since the adhesive force between the base material layer 1 and the semiconductor wafer is lower than that between the adhesive layer 2 and the semiconductor wafer, it is preferred. This adhesive force is, for example, 0 to 5.9 N/200 mm, more preferably 0.1 to 3 N/200 mm, and even more preferably 0.5 to 2 N/200 mm. The adhesive force is, specifically for example, 0, 0.1, 0.5, 1.0, 1.5, 2.0, 2.5, 3.0, 3.5, 4.0, 4.5, 5.0, 5.5, or 5.9 N/200 mm, and may be in the range between the two values exemplified herein. In addition, the adhesive force under the above-described measurement conditions before heating is preferably 5 N/200 mm or lower. This adhesive force is, for example, 0 to 5 N/200 mm, specifically for example, 0, 0.1, 0.5, 1, 2, 3, 4, or 5 N/200 mm, and may be in the range between the two values exemplified herein.

[0027]

The acrylic resin means a resin in which the ratio of the (meth)acrylic monomer unit contained in the resin is 50 mass% or more. The (meth)acrylic monomer means a compound having a

(meth)acryloyl group. The (meth)acrylic monomer is preferably monofunctional.

[0028]

Examples of the (meth)acrylic monomer include (meth)acrylic acids and/or (meth)acrylic esters. Examples of the (meth)acrylic ester include alkyl (meth)acrylates, hydroxyalkyl (meth)acrylates, and (meth)acrylates having a cyclic ether skeleton. These may be used alone or in combination.

[0029]

As the alkyl (meth)acrylate, (meth)acrylates represented by the general formula (A) shown below are preferred.

[0030]

(A) $Z-O-R$

In the general formula, Z represents a (meth)acryloyl group, and R represents an alkyl group having 1 to 10 carbon atoms.

[0031]

Examples of such alkyl (meth)acrylates include methyl (meth)acrylate, ethyl (meth)acrylate, propyl (meth)acrylate, 2-ethylhexyl (meth)acrylate, isopropyl (meth)acrylate, butyl (meth)acrylate, isobutyl (meth)acrylate, isooctyl (meth)acrylate, isononyl (meth)acrylate, lauryl (meth)acrylate, and dodecyl (meth)acrylate.

[0032]

Examples of the hydroxyalkyl (meth)acrylate include 2-hydroxypropyl (meth)acrylate, 2-hydroxybutyl (meth)acrylate, 2-hydroxyethyl (meth)acrylate, and glycerol mono (meth)acrylate.

[0033]

Examples of the (meth)acrylate having a cyclic ether skeleton include glycidyl (meth)acrylate, furfuryl (meth)acrylate, tetrahydrofuryl (meth)acrylate, 3-ethyl-3-oxetanyl methyl (meth)acrylate, (2-methyl-ethyl-1,3-dioxolan-4-yl)methyl (meth)acrylate, cyclic trimethylolpropane formal (meth)acrylate, γ -butyrolactone (meth)acrylate, dioxolane (meth)acrylate, dioxane glycol di(meth)acrylate, and oxetane (meth)acrylate. One or more kinds of these can be used. Among cyclic ether skeletons, 5 to 6 membered rings are preferred. The cyclic ether skeleton preferably has one oxygen atom. The cyclic ether skeleton preferably has 2 to 5 carbon atoms. Among (meth)acrylates having a cyclic ether skeleton, glycidyl (meth)acrylate is preferred.

[0034]

The acrylic resin may contain only (meth)acrylic monomer unit, or other monomer units other than the (meth)acrylic monomer unit. Examples of other monomer units include olefins such as ethylene and propylene, aliphatic vinyls such as vinyl acetate, and aromatic vinyls such as styrene.

[0035]

The ratio of the (meth)acrylic monomer unit in the acrylic resin configuring the surface treatment layer 1b is, for example, 50 to 100 mass%, specifically for example, 50, 55, 60, 65, 70, 75, 80, 85, 90, 95, or 100 mass%, and may be in the range between the two values exemplified herein.

[0036]

The acrylic resin can be obtained by polymerizing a monomer mixture containing the above-described monomer.
[0037]

The acrylic resin composition preferably contains a cross-linking agent. The acrylic resin is cross-linked by the reaction of the acrylic resin and the cross-linking agent. Examples of the cross-linking agent include acrylate-based cross-linking agents, isocyanate-based cross-linking agents, epoxy-based cross-linking agents, and amine-based cross-linking agents. These may be used alone, or two or more kinds of these may be used in combination.
[0038]

Examples of the acrylate-based cross-linking agent include compounds having a plurality of (e.g., two) (meth)acryloyl groups, such as 1,9-nonanediol diacrylate, 1,6-hexanediol diacrylate, triethylene glycol diacrylate, polytetramethylene glycol diacrylate, neopentyl glycol diacrylate, and 3-methyl-1,5-pentanediol diacrylate.
[0039]

Examples of the isocyanate-based cross-linking agent include multivalent isocyanate compounds such as 2,4-tolylenediisocyanate, 2,6-tolylenediisocyanate, 1,3-xylylenediisocyanate, 1,4-xylenediisocyanate, diphenylmethane-4,4'-diisocyanate, diphenylmethane-2,4'-diisocyanate, 3-methyl diphenylmethane diisocyanate, hexamethylene diisocyanate, isophorone diisocyanate, dicyclohexylmethane-4,4'-diisocyanate, dicyclohexylmethane-2,4'-diisocyanate, and lysine isocyanate; and derivatives thereof (adduct product, biuret product, isocyanurate product). These may be used alone, or two or more kinds of these may be used in combination.
[0040]

The blending amount of the cross-linking agent to 100 parts by mass of the acrylic resin is, for example, 0.5 to 30 parts by mass, preferably 4 to 25 parts by mass, and more preferably 7 to 20 parts by mass. The blending amount is, specifically for example, 0.5, 1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 15, 20, 25, or 30 parts by mass, and may be in the range between the two values exemplified herein.
[0041]

The acrylic resin is cross-linked by light irradiation or heating.
[0042]

In the case of cross-linking by light irradiation, the acrylic resin composition preferably contains a photopolymerization initiator. Specific examples of the photopolymerization initiator that can be used include benzoin ether-based photopolymerization initiators, acetophenone-based photopolymerization initiators, α -ketol-based photopolymerization initiators, aromatic sulfonyl chloride-based photopolymerization initiators, photoactive oxime-based photopolymerization initiators, benzoin-based photopolymerization initiators, benzyl-based photopolymerization initiators, benzophenone-based photopolymerization initiators, ketal-based photopolymerization

initiators, thioxanthone-based photopolymerization initiators, and acylphosphine oxide-based photopolymerization initiators, but are not limited thereto. The acetophenone-based photopolymerization initiators are preferred.

[0043]

Specific examples of the acetophenone-based photopolymerization initiator include 1-hydroxycyclohexylphenyl ketone, 4-phenoxydichloroacetophenone, 4-*t*-butyl-dichloroacetophenone, 1-[4-(2-hydroxyethoxy)-phenyl]-2-hydroxy-2-methyl-1-propan-1-one, 2-hydroxy-2-methyl-1-phenyl-propan-1-one, and methoxyacetophenone.

[0044]

The Mw of the acrylic resin before cross-linking is preferably 300000 to 2000000, and more preferably 450000 to 800000. When the Mw is too low, the heat resistance may be insufficient. When the Mw is too high, the viscosity may be too high, making coating difficult and thus reducing productivity. The Mw is, specifically for example, 300000, 350000, 400000, 450000, 500000, 550000, 600000, 650000, 700000, 750000, 800000, 900000, 1000000, 1100000, 1200000, 1300000, 1400000, 1500000, 1600000, 1700000, 1800000, 1900000, or 2000000, and may be in the range between the two values exemplified herein.

[0045]

The glass transition temperature (Tg) of the acrylic resin before cross-linking is preferably -15 to 40°C, and more preferably -10 to 30°C. This Tg is, specifically for example, -15, -10, -5, 0, 5, 10, 15, 20, 25, 30, 35, or 40°C, and may be in the range between the two values exemplified herein. The glass transition temperature (Tg) of the acrylic resin after cross-linking is preferably 10 to 80°C, and more preferably 20 to 70°C. This Tg is, specifically for example, 10, 15, 20, 25, 30, 35, 40, 45, 50, 55, 60, 65, 70, 75, or 80°C, and may be in the range between the two values exemplified herein.

[0046]

In the present specification, the Tg is measured as follows. Differential scanning calorimetry (DSC) measurement is performed in accordance with JIS K 7121: 1987. Then, the intersection of the tangent line of the baseline in the DSC curve and the tangent line of the steeply descending position of the endothermic region due to glass transition is taken as the Tg.

[0047]

The storage modulus at 180°C of the surface treatment layer 1b is preferably 1.0×10^4 Pa to 1.0×10^8 Pa. If the storage modulus is too low, the surface treatment layer 1b becomes too soft by heating the adhesive sheet 10 when a wafer is adhered to the adhesive sheet 10. As a result, the surface treatment layer 1b may break as the cushion layer 1a melts, leaving residue of the surface treatment layer 1b on the wafer and impairing peelability. If the storage modulus is too high, the surface treatment layer 1b may be too hard, which may deteriorate the followability of the base material layer 1 to the convex part 5.

[0048]

The storage modulus is, specifically for example, 1.0×10^4 Pa, 1.0×10^5 Pa, 1.0×10^6 Pa, 1.0×10^7 Pa, or 1.0×10^8 Pa, and may be in the range between the two values exemplified herein.

[0049]

The thickness of the surface treatment layer 1b is, for example, 0.1 to 10 μm , preferably 0.5 to 5 μm , and more preferably 1 to 4 μm . When the surface treatment layer 1b has such a thickness, the effect of providing the surface treatment layer 1b is likely to be exhibited properly. The thickness is, specifically for example, 0.1, 0.5, 1.0, 1.5, 2.0, 2.5, 3.0, 3.5, 4.0, 5.0, 6.0, 7.0, 8.0, 9.0, or 10.0 μm , and may be in the range between the two values exemplified herein.

[0050]

<Barrier Layer 1c>

The barrier layer 1c is a layer to reduce the oxygen permeability of the base material layer 1. When the base material layer 1 is easily permeable to air, outside air may enter a sealed space 2b through the base material layer 1, making it difficult to depressurize the sealed space 2b, which may result in the deterioration of the followability of the base material layer 1 to the convex part 5.

[0051]

The barrier layer 1c is a layer with low oxygen permeability. When oxygen permeability is low, air permeability is also normally low. Therefore, outside air is suppressed from entering the sealed space 2b through the base material layer 1 by providing the barrier layer 1c, thereby exhibiting the effect that the base material layer 1 becomes easy to follow the convex part 5.

[0052]

Preferably, the barrier layer 1c is provided so that the oxygen permeability of the base material 1 at 25°C and at RH0%, which is measured based on JIS K 7126-2 (isobaric method), is 1000 ml/(m²·24h·atm) or lower. Preferably, the oxygen permeability of the barrier layer 1c alone under the same conditions is 1000 ml/(m²·24h·atm) or lower to make the oxygen permeability of the base material 1 within such a range. In this case, the above-described effect is likely to be exhibited. The oxygen permeability of the base material 1 or the barrier layer 1c is, for example, 0 to 1000 ml/(m²·24h·atm), preferably 0 to 500 ml/(m²·24h·atm), specifically for example, 0, 100, 200, 300, 400, 500, 600, 700, 800, 900, or 1000 ml/(m²·24h·atm), and may be in the range between the two values exemplified herein.

[0053]

The oxygen permeability of the barrier layer 1c under the above-described conditions is preferably lower than that of the cushion layer 1a. The value of (oxygen permeability of the cushion layer 1a - oxygen permeability of the barrier layer 1c) is preferably 100 ml/(m²·24h·atm) or higher. The value is, for example, 100 to 3000 ml/(m²·24h·atm), specifically for example, 100, 500, 1000, 1500, 2000, 2500, or 3000 ml/(m²·24h·atm), and may be in the range between the two values exemplified herein.

[0054]

The barrier layer 1c can be formed of any material capable of achieve the above-described oxygen permeability, and polyester (e.g., polyethylene terephthalate), polyimide, and polyamide are preferred from the viewpoint of easily reducing the oxygen permeability.

[0055]

The thickness of the barrier layer 1c is, for example, 5 to 50 μm , and preferably 10 to 30 μm . When the barrier layer 1c is too thin, the oxygen permeability of the base material layer 1 may not be sufficiently low. When the barrier layer 1c is too thick, the followability of the base material 1 to the convex part 5 may deteriorate. The thickness is, specifically for example, 5, 10, 15, 20, 25, 30, 35, 40, 45, or 50 μm , and may be in the range between the two values exemplified herein.

[0056]

2. Adhesive Layer 2

The adhesive layer 2 is a layer for adhering the adhesive sheet 10 to the semiconductor wafer 4, and is formed of an adhesive. The adhesive layer 2 has an opening part 2a with a diameter smaller than the diameter of the semiconductor wafer 4. In other words, the adhesive layer 2 is ring-shaped. The opening part 2a is a part where no adhesive is provided, and has a diameter smaller than the diameter of the semiconductor wafer 4. The diameter of the opening part 2a / diameter of the semiconductor wafer 4 is preferably 0.950 to 0.995, and more preferably 0.960 to 0.990.

[0057]

The adhesive layer 2 is adhered to an outer peripheral part 4a of the semiconductor wafer 4 so that the convex part 5 of the wafer 4 is placed in the opening part 2a. Therefore, the convex part 5 is not in contact with the adhesive, and adhesive residue on the convex part 5 is prevented.

[0058]

The width of the adhesive layer 2 is preferably 10 to 100 mm, and more preferably 30 to 70 mm. The thickness of the adhesive layer 2 is preferably 1 to 100 μm , and more preferably 5 to 50 μm . The thickness is, specifically for example, 1, 5, 10, 15, 20, 25, 30, 35, 40, 45, 50, 100 μm , and may be in the range between the two values exemplified herein.

[0059]

The adhesive layer 2 is preferably formed of an acrylic resin composition containing an acrylic resin. The composition of the acrylic resin of the adhesive layer 2 may be the same as or different from that of the acrylic resin of the surface treatment layer 1b.

[0060]

The ratio of the (meth)acrylic monomer unit contained in the acrylic resin configuring the adhesive layer 2 is, for example, 50 to 100 mass%, specifically for example, 50, 55, 60, 65, 70, 75, 80, 85, 90, 95, or 100 mass%, and may be in the range between the two values exemplified herein.

[0061]

Examples of the (meth)acrylic monomer include monomers having hydroxyl groups such as 2-hydroxyethyl (meth)acrylate, 2-hydroxypropyl (meth)acrylate, and 2-hydroxybutyl (meth)acrylate; monomers having carboxyl groups such as (meth)acrylic acid, crotonic acid, maleic acid, itaconic acid, fumaric acid, acrylamide N-glycolic acid, and cinnamic acid; and monomers having epoxy groups such as allyl glycidyl ether, and (meth)acrylic acid glycidyl ether, as a (meth)acrylic monomer or monomer containing functional groups such as butyl (meth)acrylate, 2-butyl (meth)acrylate, t-butyl (meth)acrylate, pentyl (meth)acrylate, octyl (meth)acrylate, 2-ethylhexyl (meth)acrylate, nonyl (meth)acrylate, decyl (meth)acrylate, lauryl (meth)acrylate, methyl (meth)acrylate, ethyl (meth)acrylate, isopropyl (meth)acrylate, tridecyl (meth)acrylate, myristyl (meth)acrylate, cetyl (meth)acrylate, stearyl (meth)acrylate, cyclohexyl (meth)acrylate, benzyl (meth)acrylate, dimethyl acrylamide, diethyl acrylamide, acryloyl morpholine, and isobornyl acrylate.

[0062]

The cross-linking agent is preferably blended in the acrylic resin composition configuring the adhesive layer 2. Examples of the cross-linking agent include polyfunctional isocyanate cross-linking agents and polyfunctional epoxy cross-linking agents. When the cross-linking agent reacts with the functional group, the cross-linked structure with the functional groups as base points is formed, which increases cohesive force of the adhesive and suppresses adhesive residue. In addition, (meth)acrylate with one or more (meth)acroylated ends or side chains of oligomer/polymer such as 1,2-polybutadiene-terminated urethane (meth)acrylate, hydrogenated product thereof, 1,4-polybutadiene-terminated urethane (meth)acrylate, polyisoprene-terminated (meth)acrylate, polyester-based urethane (meth)acrylate, polyether-based urethane (meth)acrylate, polyester (meth)acrylate, and bis-A epoxy (meth)acrylate may be used.

[0063]

The blending amount of the cross-linking agent to 100 parts by mass of the acrylic resin is, for example, 0.1 to 10 parts by mass, preferably 0.5 to 8 parts by mass, and more preferably 1 to 6 parts by mass. The blending amount is, specifically for example, 0.1, 0.5, 1.0, 1.5, 2.0, 2.5, 3.0, 3.5, 4.0, 4.5, 5.0, 5.5, 6.0, 6.5, 7.0, 7.5, 8.0, 8.5, 9.0, 9.5, or 10.0 parts by mass, and may be in the range between the two values exemplified herein.

[0064]

The glass transition temperature (T_g) of the acrylic resin after cross-linking is preferably -30 to 5°C, and more preferably -25 to -5°C. The T_g is, specifically for example, -30, -25, -20, -15, -10, -5, 0, or 5°C, and may be in the range between the two values exemplified herein.

[0065]

The adhesive layer 2 can be formed by applying the adhesive onto the base material layer 1 for coating, or by applying the adhesive onto a release film and then transferring it to the base

material layer 1, for example, using a general coating method such as comma coating, gravure coating, roll coating, and screen coating.

[0066]

The adhesive force measured in accordance with JIS Z0237 at 23°C between the adhesive layer 2 and the semiconductor wafer after heating the semiconductor wafer to which the adhesive layer 2 is adhered for 1 minute at 100°C and cooling to room temperature is preferably 6 to 50 N/200 mm, and more preferably 10 to 30 N/200 mm. In addition, the adhesive force under the above-described measurement conditions before heating is preferably 6 N/200 mm or higher, for example, 6 to 50 N/200 mm. These adhesive forces are, specifically for example, 6, 10, 15, 20, 25, 30, 35, 40, 45, or 50 N/200 mm, and may be in the range between the two values exemplified herein.

[0067]

<Semiconductor Wafer 4>

The semiconductor wafer 4 has a convex part 5. The convex part 5 is an arbitrary structure that protrudes in the out-of-plane direction of the semiconductor wafer 4. Examples of the convex part 5 include a protruding electrode, and the convex part of a circuit having unevenness.

[0068]

Examples of the semiconductor wafer 4 include not only a silicon wafer but also a germanium wafer, a gallium-arsenide wafer, a gallium-phosphorus wafer, and a gallium-arsenide aluminum wafer. The diameter of the semiconductor wafer 4 is preferably 1 to 16 inches, and more preferably 4 to 12 inches. The thickness of the semiconductor wafer 4 is preferably 500 to 800 μm , and more preferably 520 to 775 μm , but is not limited thereto.

[0069]

The height of the convex part 5 is preferably 10 to 500 μm , and more preferably 100 to 300 μm . The height is, specifically for example, 10, 50, 100, 150, 200, 250, 300, 350, 400, 450, or 500 μm , and may be in the range between the two values exemplified herein.

[0070]

The semiconductor wafer 4 preferably has the outer peripheral part 4a where the convex part 5 is not provided. The width of the outer peripheral part 4a is preferably 1.0 to 3.0 mm, and more preferably 1.5 to 2.5 mm.

[0071]

Examples of final products using the semiconductor wafers 4 having the convex part 5 include electronic components for logic, memory, sensor, power supply, or the like.

[0072]

<Curable Resin 8>

The curable resin 8 is a resin that is cured by stimulus such as energy rays (e.g., ultraviolet rays) or heat. The curable resin 8 is placed between the cushion layer 1 and a support film 7.

[0073]

The viscosity of the curable resin 8 before curing is preferably 100 to 3000 mPa·s, and more preferably 200 to 1000 mPa·s.

When the viscosity is 100 mPa·s or higher, the curable resin 8 has not a surface contact but a point contact, which suppresses air bubble mixing in the pressing step, resulting in excellent grindability. When the viscosity is 3000 mPa·s or lower, the curable resin 8 is less likely to entangle air bubbles when it flows between the adjacent convex parts 5, resulting in excellent grindability. The viscosity is measured using an E-type viscometer under the conditions of 23°C and 50 rpm.
[0074]

The Shore D hardness of the curable resin 8 after curing is preferably 5 to 70, and more preferably 10 to 60. When the Shore D hardness is 5 or more, the retentivity of the convex part 5 is high, resulting in excellent grindability. When the Shore D hardness is 70 or less, it is easy to bend the adhesive sheet 10 when peeling the adhesive sheet 10 from the semiconductor wafer 4. The Shore D hardness is measured under the conditions in accordance with JIS K 6253.
[0075]

The curable resin 8 is preferably a light curable resin, and more preferably a UV curable resin.
[0076]

The curable resin 8 is preferably based on an acrylic resin, and the composition thereof is not particularly limited. The curable resin containing 1,2-hydrogenated polybutadiene-terminated urethane (meth)acrylate, isobornyl acrylate, and diethylacrylamide is preferred because it can improve the adhesion between the base material layer 1 and the support film 7.
[0077]

Curing shrinkage rate of the curable resin 8 is preferably 7% or less.
[0078]

When the height of the convex part 5 is taken as T_d (μm), the thickness of the curable resin 8 is preferably (T_d+20) to (T_d+200) μm , and more preferably (T_d+50) to (T_d+150) μm .
[0079]

<Support Film 7>

The support film 7 is an arbitrary film that can support the curable resin 8 and can be formed of polyolefin such as ethylene vinyl acetate, polyethylene, polypropylene, polybutene, and polybutadiene, or polyvinyl chloride, polyethylene terephthalate, polyethylene naphthalate, polystyrene, polycarbonate, polyimide, or the like.
[0080]

The thickness of the support film 7 is preferably 10 to 300 μm , and more preferably 30 to 250 μm .
[0081]

2. Method for Manufacturing Semiconductor Wafer

Figs. 1 to 9 illustrate a method for manufacturing a semiconductor wafer using the adhesive sheet 10. This method includes a frame adhering step, a heating step, a cutting step, a resin curing step, a grinding step, and a peeling step. The order in which these steps are performed is not limited thereto, and the

order can be exchanged as appropriate. Hereinafter, each step will be described.

[0082]

<Frame Adhering Step>

As shown in Figs. 1 to 2, in the frame adhering step, the adhesive sheet 10 is adhered to the ring frame 3. The ring frame 3 has an opening part 3a having a diameter larger than the diameter of the opening part 2a of the adhesive layer 2, and the ring frame 3 can be adhered to the adhesive layer 2. This allows the adhesive sheet 10 to be held stably by the ring frame 3, making it easier to handle the adhesive sheet 10.

[0083]

<Wafer Adhering Step and Heating Step>

As shown in Figs. 2 to 3, in the wafer adhering step, the adhesive sheet 10 is adhered to the outer peripheral part 4a of the semiconductor wafer 4 under reduced pressure, the outer peripheral part 4a on the surface of the semiconductor wafer 4 where the convex part 5 is provided. The width of the adhering surface where the semiconductor wafer 4 is adhered to the adhesive layer 2 is preferably 1.0 to 3.0 mm, and more preferably 1.5 to 2.5 mm.

[0084]

This step can be performed by adhering the adhesive sheet 10 to the semiconductor wafer 4 in a decompression chamber 16. The pressure in the decompression chamber 16 should be lower than atmospheric pressure, preferably 1000 Pa or lower, more preferably 500 Pa or lower, and even more preferably 100 Pa or lower. The lower limit of the pressure in the decompression chamber 16 is, for example, 10 Pa, but is not limited thereto.

[0085]

By adhering the adhesive sheet 10 to the semiconductor wafer 4 under reduced pressure in this way, the inside of the sealed space 2b surrounded by the semiconductor wafer 4 and the adhesive sheet 10 becomes in a depressurized state.

[0086]

In that state, when the adhesive sheet 10 adhered to the semiconductor wafer 4 is removed from the decompression chamber 16 and exposed to atmospheric pressure, the base material layer 1 is pushed by atmospheric pressure and attempts to enter the inside of the sealed space 2b. When the base material layer 1 is not in a heated state, it has high rigidity and therefore hardly enters the sealed space 2b. On the other hand, in the heating step, when the base material layer 1 is heated to 60 to 150°C, the base material layer 1 is softened and enters the inside of the sealed space 2b, as shown in Fig. 4. As a result, the convex part 5 is embedded in the base material layer 1, and the convex part 5 is protected by the base material layer 1. The ratio of the height of the embedded part of the convex part 5 / the entire height of the convex part 5 is preferably 0.2 to 1, more preferably 0.5 to 1, and even more preferably 0.8 to 1. The heating temperature of the base material layer 1 is preferably 80 to 120°C. The heating time of the base

material layer 1 is preferably 3 to 120 seconds, and more preferably 5 to 60 seconds.

[0087]

The heating of the base material layer 1 may be performed before or after adhering the semiconductor wafer 4 to the adhesive sheet 10. The heating may be performed inside or outside the decompression chamber 16.

[0088]

<Cutting Step>

As shown in Figs. 4 to 5, in the cutting step, the adhesive sheet 10 is cut along the outer periphery of the semiconductor wafer 4. As a result, the adhesive sheet 10 adhered to the semiconductor wafer 4 is separated from the ring frame 3. The cutting step can be performed after the resin curing step.

[0089]

<Resin Curing Step>

In the resin curing step, the base material layer 1 is brought in contact with the curable resin 8 after the wafer adhering step, and the curable resin 8 is cured in that state. In an example, this step can be performed by the following method.

[0090]

First, as shown in Figs. 5 to 6, the curable resin 8 is pressed and spread by moving the adhesive sheet 10 with the adhesive sheet 10 facing the curable resin 8 supplied on the support film 7.

[0091]

In an example, the semiconductor wafer 4 is sucked on the decompression unit 6 having decompression holes 6a, and the adhesive sheet 10 is pressed against the curable resin 8 in that state. In that state, the curable resin 8 is pressed and spread by moving the adhesive sheet 10 along the surface of the support film 7.

[0092]

Next, as shown in Figs. 6 to 7, the curable resin 8 is cured with the base material layer 1 in contact with the curable resin 8.

[0093]

In an example, the curable resin 8 can be cured into a cured resin 18 by irradiating the curable resin 8 with energy rays 9 such as ultraviolet rays through the support film 7. This allows the adhesive sheet 10 to be held stably on the support film 7.

[0094]

<Grinding Step>

As shown in Figs. 7 to 8, the backside 4b of the semiconductor wafer 4 is ground in the grinding step.

[0095]

The backside 4b of the semiconductor wafer 4 is a surface opposite to the surface where the convex part 5 is provided. There are no restrictions on the methods for grinding the backside of the wafer, and any known grinding method can be used. The grinding is preferably performed while water is applied to the wafer and a grinding wheel (e.g., diamond wheel) to cool them down. The

thickness of the wafer that was made thinner by the grinding is preferably 300 μm or smaller, and more preferably 50 μm or smaller.

[0096]

During back grinding, the convex part 5 is easily damaged because an in-plane directional load of the semiconductor wafer 4 is applied to the convex part 5. However, in the present embodiment, since at least a part of the convex part 5 is embedded in the base material layer 1 and the curable resin 8 cured, the convex part 5 is stably supported by the base material layer 1 and the curable resin 8 cured, and therefore the convex part 5 is hardly damaged.

[0097]

<Peeling Step>

As shown in Figs. 8 to 9, in the peeling step, the adhesive sheet 10 is peeled from the semiconductor wafer 4. The peeling of the adhesive sheet 10 can be performed by bending the adhesive sheet 10 in the direction in which the sheet 10 moves away from the semiconductor wafer 4.

[0098]

This completes the back grinding step of the semiconductor wafer 4. When the back grinding is performed using an adhesive sheet in such a form where the convex part 5 is in contact with the adhesive, the adhesive may be adhered to the convex part 5. However, in the present embodiment, adhesion of the adhesive to the convex part 5 is suppressed because the convex part 5 is not in contact with the adhesive layer 2.

[0099]

The dicing step may be performed before the peeling step. In the dicing step, the semiconductor wafer 4 is divided into a plurality of semiconductor chips by dicing the semiconductor wafer 4. The dicing method is not particularly limited, and may be any method such as blade dicing, laser dicing, stealth dicing, and plasma dicing.

[0100]

When the dicing step is performed, a plurality of semiconductor chips is adhered to the adhesive sheet 10. Therefore, the peeling step is a step where each of the plurality of semiconductor chips is peeled from the adhesive sheet 10.

[0101]

3. Base Material Sheet

As shown in Fig. 10, the base material sheet 11 of one embodiment of the present invention can have the same configuration as that of the base material layer 1. In other words, the base material sheet 11 has the cushion layer 1a and the barrier layer 1c, and the oxygen permeability measured at 25°C and at RH0% based on JIS K 7126-2 (isobaric method) is 1000 $\text{ml}/(\text{m}^2 \cdot 24\text{h} \cdot \text{atm})$ or lower. The base material sheet 11 may have the surface treatment layer 1b. The descriptions of the base material layer 1, the cushion layer 1a, the surface treatment layer 1b, and the barrier layer 1c are the same as those in "1-1. Base Material Layer 1".

[0102]

The base material sheet 11 can be used as the base material layer 1 of the adhesive sheet 10 for back grinding of the semiconductor wafer 4 having the convex part 5. The base material sheet 11 can also be used as a sheet for grinding the backside of the semiconductor wafer 4 having the convex part 5 without providing the adhesive layer 2 in the adhesive sheet 11. In this case, for example, the base material sheet 11 can be adhered to the semiconductor wafer 4 by the action of atmospheric pressure, by removing the base material sheet 11 and the semiconductor wafer 4 from the decompression chamber 16 after depressurizing the inside of the sealed space 2b formed by pressing the base material sheet 11 against the semiconductor wafer 4 in the decompression chamber 16 as described above in <Wafer Adhering Step and Heating Step> in "2. Method for Manufacturing Semiconductor Wafer". A ring-shaped packing having the same shape as the adhesive layer 2 may be placed between the base material sheet 11 and the semiconductor wafer 4 to form the sealed space 2b.

Example

[0103]

1. Manufacture of Adhesive Sheet 10

<Example 1>

In Example 1, the adhesive sheet 10 was manufactured by laminating the barrier layer 1c and the cushion layer 1a to form the base material layer 1 and forming the ring-shaped adhesive layer 2 having the opening part 2a on the cushion layer 1a.

[0104]

More detailed descriptions are as follows.

[0105]

-Preparation of Cushion Layer 1a

First, the cushion layer 1a configured of a 150 μm -thick metal ion cross-linked material of the ethylene-methacrylic acid copolymer (FUNCRARE HMD, made by Gunze Limited) was prepared. The ethylene-methacrylic acid copolymer had a methacrylic acid unit ratio of 15 mass%, an MFR (JIS K7210, 125°C/10.0 kg load) of 5 g/10 min, and a melting point (JIS K7121) of 72°C.

[0106]

-Formation of Base Material Layer 1

First, as constituent monomers, 70 parts by mass of butyl acrylate, 22 parts by mass of methyl methacrylate, 5 parts by mass of 2-hydroxyethyl methacrylate, and 3 parts by mass of the glycidyl methacrylate monomer was polymerized to obtain the acrylic copolymer. To 100 parts by mass of this acrylic copolymer, 4 parts by mass of the isocyanate cross-linking agent (CORONATE L-45E, made by Nippon Polyurethane Industry Co., Ltd.) was added to obtain the adhesive.

[0107]

For coating, the above-described adhesive was then applied onto the barrier layer 1c configured of the 25 μm -thick PET film (Lumirror S10, made by Toray Industries, Inc.). It was dried at 100°C for 1 minute to form the 10 μm -thick adhesive layer.

[0108]

Next, the cushion layer 1a was laminated on the adhesive layer, and aging was performed in an atmosphere at 40°C for 72 hours to form the base material layer 1.

[0109]

-Formation of Adhesive Layer 2

54.4 parts by mass of hydrogenated polybutadiene diacrylate (product name: BAC-45, made by OSAKA ORGANIC CHEMICAL INDUSTRY LTD.), 13.6 parts by mass of isodecyl acrylate (product name: IDAA, made by OSAKA ORGANIC CHEMICAL INDUSTRY LTD.), 32 parts by mass of isobonyl acrylate (product name: IBXA, made by OSAKA ORGANIC CHEMICAL INDUSTRY LTD.), 7 parts by mass of α -aminoalkylphenone (product name: Omnilad 379EG, made by BASF) as photopolymerization initiator, 3 parts by mass of vinyl ether polymer (FLOWLEN AC-903, made by KYOEISHA CHEMICAL Co., Ltd) as an antifoaming agent, and 3 parts by mass of isocyanate (product name: TPA-100, made by Asahi Kasei Corp.) as a cross-linking agent were added to prepare the liquid composition. This composition was screen-printed on the base material layer 1 in a specific shape, and after UV irradiation, aging was performed at 40°C for 4 days to form the 10 μ m-thick ring-shaped adhesive layer 2.

[0110]

<Example 2>

The adhesive sheet 10 was manufactured in the same way as in Example 1, except that the 15 μ m-thick PA film (Harden N1202, made by TOYOBO CO., LTD.) was used as the barrier layer 1c.

[0111]

<Example 3>

The adhesive sheet 10 was manufactured in the same way as in Example 1, except that the 12 μ m-thick PI film (Kapton EN, made by DU PONT-TORAY CO., LTD.) was used as the barrier layer 1c.

[0112]

<Comparative Example 1>

The adhesive sheet 10 was manufactured in the same way as in Example 1, except that the cushion layer 1a was used as the base material layer 1 as it is, without forming the barrier layer 1c.

[0113]

<Comparative Example 2>

The adhesive sheet 10 was manufactured in the same way as in Example 1, except that the 30 μ m-thick PC film (LUCKRON AA, International Chemical Co., ltd) was used as the barrier layer 1c.

[0114]

2. Back Grinding of Semiconductor Wafer

The back grinding of semiconductor wafer 4 was performed by the following method using the adhesive sheet 10 as prepared above.

[0115]

<Frame Adhering Step>

First, the adhesive sheet 10 is adhered to the ring frame 3.

[0116]

<Wafer Adhering Step and Heating Step>

Next, the adhesive sheet 10 was adhered to the outer peripheral part 4a of the semiconductor 4 in the decompression chamber 16, the outer peripheral part 4a on the surface where the convex part 5 was provided. Used was the semiconductor wafer 4 having a diameter of 8 inches and a thickness of 725 μm , in which a bump (protruding electrode) with a height of 90 μm was formed in the region excluding the outer peripheral part with a width of 3.0 mm. The width of the adhering surface where the semiconductor wafer 4 was adhered to the adhesive layer 2 was 2.0 mm. The pressure in the decompression chamber 16 was 100 Pa. The base material layer 1 was heated to 100°C in the decompression chamber 16.

[0117]

Next, the adhesive sheet 10 with the semiconductor wafer 4 adhered was removed from the decompression chamber 16.

[0118]

<Cutting Step>

Next, the ring frame 3 was separated from the adhesive sheet 10 by cutting the adhesive sheet 10 along the outer periphery of the semiconductor wafer 4.

[0119]

<Resin Curing Step>

Next, the curable resin 8 was pressed and spread by moving the adhesive sheet 10 in the in-plane direction of the support film 7 with the adhesive sheet 10 facing the curable resin 8 supplied on the support film 7. Used was the curable resin 8 configured of 1,2-hydrogenated polybutadiene-terminated urethane (meth) acrylate, isobornyl acrylate, and diethylacrylamide. The viscosity of the curable resin 8 before curing (measured using an E-type viscometer under the conditions of 23°C and 50 rpm) was 470 mPa·s.

[0120]

Next, the curable resin 8 was cured with the base material layer 1 in contact with the curable resin 8, and was made into the cured resin 18. The curable resin 8 was cured by irradiating the curable resin from the side of the support film 7 with ultraviolet rays so that the integrated light quantity at a wavelength of 365 nm became 2000 mJ/cm². The Shore D hardness (JIS K 6253) of the cured resin 18 was 15.

[0121]

<Grinding Step>

Next, back grinding of the semiconductor wafer 4 was performed until the thickness of the semiconductor wafer 4 became 100 μm . The back grinding was performed using a polishing machine (back grinder DFG-841, made by DISCO Corporation).

[0122]

<Dicing Step>

Next, the semiconductor wafer 4 after back grinding was divided into 0.49 mm × 0.3 mm semiconductor chips by dicing.

[0123]

Dicing was performed by rotating a dicing blade containing diamond abrasive grains at high speed using a dicing machine. The main settings for dicing are as follows.

Dicing equipment: DAD341, made by DISCO Corporation
Dicing blade: NBC-ZH2050-27HEE, made by DISCO Corporation
Dicing blade rotation speed: 40000 rpm
Dicing blade feed speed: 50 mm/s
Cutting water temperature: 25°C
Cutting water amount: 1.0 L/min

[0124]

<Peeling Step>

Next, the semiconductor chip was peeled from the adhesive sheet 10.

[0125]

3. Evaluation

Each evaluation was conducted for the manufactured adhesive sheet 10. The results are shown in Table 1.

[0126]

As shown in Table 1, good results were obtained for all evaluation items in all Examples. In Comparative Examples 1 to 2 where the oxygen permeability of the base material layer 1 was high, the bump followability and chip contamination resistance were insufficient.

[0127]

[Table 1]

Table 1		Example			Comparative Example	
		1	2	3	1	2
Barrier Layer		PET25	PA15	PI12	-	PC30
Evaluation	Bump Followability	Excellent	Excellent	Excellent	Bad	Good
	Chip Contamination Resistance	Excellent	Excellent	Excellent	Bad	Bad
	Adhesive Force between Base Material and Wafer (N/200 mm)	28	25	24	21	30
	Oxygen Permeability of Base Material Layer ml/(m ² ·24h·atm)	<100	<100	300	2248	1400

[0128]

Details of the evaluation method are as follows.

<Bump Followability>

The bump followability was evaluated by the following method.

[0129]

The distance that the base material layer 1 followed between bumps was measured for the adhesive sheet 10 to which the semiconductor wafer 4 was adhered after the cutting step of "2. Back Grinding of Semiconductor Wafer" described above, and the followability rate (= distance that the base material layer 1 followed between bumps / bump height) was calculated.

[0130]

The bump followability was evaluated from the followability rate using the following criteria.

Excellent: Followability rate is 95% or more

Good: Followability rate is 71 to 94%

Bad: Followability rate is less than 70%

[0131]

<Chip Contamination Resistance>

The chip contamination resistance was evaluated using the following criteria based on whether or not the chip surface (the surface with bumps) of the semiconductor chip after the peeling step described above in "2. Back Grinding of Semiconductor Wafer" was contaminated by water or gas, which is determined by observing the chip surface using the optical microscope.

Excellent: Without contamination

Bad: With contamination

[0132]

<Adhesive Force between Base Material and Wafer>

The adhesive force between the base material layer and the wafer was measured by the following method. A test piece having a width of 10 mm and a length of 100 mm was cut from the area near the center of the adhesive sheet 10 where the adhesive layer 2 is not formed (i.e., the area where the base material layer is exposed), and this test piece was used to measure the adhesive force in accordance with the adhesive force measurement method of JIS Z0237 (2009) (Method 1: Test method in which tape and sheet are peeled at 180° to a stainless steel test plate. Specifically, using a crimping device (roller weight: 2 kg), the test piece was crimped to the adherend (Si wafer) whose surface had been cleaned, and then heated on a hot plate at 100°C for 1 minute. The adhesive force when the test piece was pulled and peeled at 180° to the adherend was measured with a universal tensile tester (ORIENTEC Tensilon Model No.: RTG-1210) at a temperature of 23°C and at a humidity of 50% using the following conditions, and converted to a value at a width of 200 mm.

Measuring mode: Tensile

Pulling speed: 300 mm/min

Distance between chucks: 50 mm

Measurement sample width: 10 mm

[0133]

<Oxygen Permeability>

The oxygen permeability of the base material layer 1 at 25°C and at RH0% (DRY) was measured by a gas chromatograph method in accordance with JIS K 7126-2 (isobaric method) using an oxygen permeability measuring equipment (GTR-10XFKS, made by GTR TEC Corporation).

Reference Signs List

[0134]

1:base material layer, 1a:cushion layer, 1b:surface treatment layer, 1c:barrier layer, 2:adhesive layer, 2a:opening part, 2b:sealed space, 3:ring frame, 3a:opening part, 4:semiconductor wafer, 4a:outer peripheral part, 4b:backside 5:convex part, 6:decompression unit, 6a:decompression hole, 7:support film 8:curable resin, 9:energy ray, 10:adhesive sheet, 11:base material sheet, 16:decompression chamber, 18:cured resin

CLAIMS

1. An adhesive sheet for back grinding of a semiconductor wafer having a convex part, comprising: a base material layer; and an adhesive layer provided on the base material layer, wherein:
 - the adhesive layer comprises an opening part having a diameter smaller than a diameter of the semiconductor wafer;
 - the adhesive layer is adhered to an outer peripheral part of the semiconductor wafer so that the convex part of the semiconductor wafer is placed in the opening part;
 - the adhesive layer is configured so that the convex part is protected by the base material layer with the semiconductor wafer adhered to the adhesive layer;
 - the base material layer comprises a cushion layer and a barrier layer; and
 - an oxygen permeability of the base material layer at 25°C and at RH0% measured base on JIS K 7126-2 (isobaric method) is 1000 ml/(m²·24h·atm) or lower.
2. The adhesive sheet of Claim 1, wherein the barrier layer is provided on an opposite side of the adhesive layer as viewed from the cushion layer.
3. The adhesive sheet of Claim 1 or 2, wherein the convex part is protected by being embedded in the base material layer.
4. The adhesive sheet of Claim 1 or 2, wherein the semiconductor wafer is adhered to the adhesive layer under reduced pressure.
5. A method for manufacturing a semiconductor wafer using the adhesive sheet of Claim 1 or 2, comprising: a frame adhering step; a wafer adhering step; a heating step; a cutting step; a resin curing step; and a grinding step, wherein:
 - in the frame adhering step, the adhesive sheet is adhered to a ring frame;
 - in the wafer adhering step, the adhesive sheet is adhered to the outer peripheral part of the semiconductor wafer under reduced pressure, the outer peripheral part on a surface of the semiconductor wafer where the convex part is provided;
 - in the heating step, the base material layer is heated;
 - in the cutting step, the adhesive sheet is cut along an outer periphery of the semiconductor wafer;
 - in the resin curing step, the base material layer is brought in contact with a curable resin after the wafer adhering step, and the curable resin is cured in that state; and
 - in the grinding step, a backside of the semiconductor wafer is ground.
6. A base material sheet, comprising: a cushion layer; and a barrier layer, wherein an oxygen permeability of the base material layer at 25°C and at RH0% measured base on JIS K 7126-2 (isobaric method) is 1000 ml/(m²·24h·atm) or lower.